# Alanya Alaaddin Keykubat University | Rafet Kayış Faculty of Engineering Electrical-Electronics Engineering Department 2023-2024 Spring Semester

| Syllabus        |   |
|-----------------|---|
| Code/Name       | EEE 204 / Semiconductor Devices and Modelling   |
| Туре            | Required  |
| Credit/ECTS     | 5/5   |
| Hour per Week   | 3(3+0+0)  |
| Level/Year      | Undergraduate/2   |
| Semester        | Spring  |
| Classroom       | A103  |
| Content         | Basic semiconductor concepts. Physical electronics. Physics of p-n junction diodes,<br>bipolar junction transistors (BJTs)and field-effect transistors. Transistor biasing and<br>small-signal models. Secondary effects in transistors. Dynamic models for diodes and<br>transistors. p-n-p-n switching devices. Modeling concepts for computer-aided design<br>and introduction to circuit analysis with computer software                          |
| Prerequisites   | None  |
| Textbooks       | <ul> <li>Primary</li> <li>A. S. Sedra &amp; A. Grabel, Microelectronic Circuits &amp; Devices, Oxford University Press, 7tht Edition, 2014</li> <li>Supplementary</li> <li>B. G. Streetman and S. Banerjee, Solid State Electronic Devices, Prentice Hall Series.</li> </ul>  |
| Objectives      | <ul> <li>To comprehend the fundamentals of solid-state electronics and semiconductor devices in order to utilize the semiconductor electron devices efficiently in discrete and integrated circuit applications</li> <li>To understand, develop and use equivalent circuit models for semiconductor devices and perform analysis of transistor amplifier circuits.</li> </ul>   |
| Course Outcomes | In this course you will be able to:<br>CO1 Understand the basic properties of semiconductors<br>CO2 Utilize widely used equivalent circuit models for semiconductor electron<br>devices to predict device behavior in electronic circuits<br>CO3 Perform small signal analysis of amplifer circuits<br>CO4 Perform computer analysis of circuits containing semiconductor devices<br>CO5 Understand and use the newly developed devices in the future |

## Weekly Schedule of Topics

| W | Topic   |  |  |  |
|---|---|--|--|--|
| 1 | Course introduction, solid-state electronic materials, bonding forces and energy bands in solids  |  |  |  |
| 2 | Impurities in semiconductors, drift and diffusion in semiconductors   |  |  |  |
| 3 | Generation-recombination of electrons and holes, continuity and diffusion equations.  |  |  |  |
| 4 | p-n junction under equilibrium and forward and reverse bias, derivation of diode current expression   |  |  |  |
| 5 | Diode I-V characteristics, p-n junction capacitance, breakdown mechanisms, dynamic switching behavior of diode, photedetectors, solar cells, LEDs |  |  |  |
| 6 | Introduction to the Bipolar Junction Transistor (BJT)   |  |  |  |
| 7 | BJT I-V characteristics and Ebers-Moll mode.  |  |  |  |
| 8 | BJT capacitances, Early Effect in BJT and BJT biasing   |  |  |  |
| 9 | MOS capacitor and introduction to MOSFET.   |  |  |  |
|   |   |  |  |  |

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- 10 MOSFET types and I-V characteristics, Body effect and channel length modulation
- 11 MOSFET biasing
- 12 MOSFET as a switching device
- 13 Small signal models for diodes and BJTS, transistor as an amplifier
- 14 The common emitter amplifier, small signal model for FETs, the common source amplifier

### **Contribution to Program Outcomes\***

|     | P01 | P02 | P03 | P04 | P05 | P06 | P07 | P08 | P09 | P010 | P011 |
|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|------|------|
| C01 | 5   | 5   | 1   | 5   | 0   | 5   | 1   | 3   | 1   | 3    | 0    |
| CO2 | 5   | 5   | 1   | 4   | 0   | 5   | 4   | 3   | 4   | 3    | 0    |
| CO3 | 5   | 5   | 3   | 5   | 2   | 5   | 1   | 3   | 1   | 3    | 0    |
| C04 | 5   | 4   | 3   | 5   | 0   | 5   | 2   | 3   | 1   | 4    | 0    |
| CO5 | 5   | 4   | 1   | 4   | 0   | 5   | 4   | 3   | 4   | 1    | 2    |

\* Contribution Level | 0: None | 1: Very Low | 2: Low | 3: Medium | 4: High | 5: Very High

| Requirements             | Basic knowledge of Electromagnetic Field Theory   |            |  |  |  |
|--------------------------|---|------------|--|--|--|
| <b>Course Policy</b>     | <ul> <li>Be in the class on time.</li> <li>English should always be used to communicate with one another</li> </ul>   |            |  |  |  |
|                          | <ul> <li>At least 70% attendance is required, otherwise a grade of <b>DZ</b> will be assigned.</li> </ul>   |            |  |  |  |
| Cheating &<br>Plagiarism | <ul> <li>Copying or letting someone copy your work on exams, assignments, or reports is cheating.</li> <li>Cutting and pasting text, figures and tables from web sources or any other electronic source is plagiarism.</li> <li>The consequence of academic dishonesty is to receive a grade of FF for the course.</li> </ul> |            |  |  |  |
| Evaluation               | Midterm <u>Final Exam</u>   | 40%<br>60% |  |  |  |
|                          | lotal   | 100%       |  |  |  |

#### Instructor

| Name/Surname | Fikri Serdar Gökhan | Email        | serdar.gokhan@alanya.edu.tr   |  |
|--------------|---------------------|--------------|-------------------------------|--|
| Room         | 209                 | Office Hours | W 11.30-12.30   F 13.30-14.30 |  |

Prepared by Akın Uslu on june 10th, 2024.